

APPLICATION NO. 10/653186

April 5, 2005

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CLMPTO

1. (Currently Amended) A semiconductor device comprising:
an insulating film which is provided in at least one layer above a substrate and whose relative dielectric constant is 3.4 or less;
at least one conductive layer provided in the insulating film;
at least one conductive plug which is formed in the insulating film and which is electrically connected to the conductive layer to form a conduction path;
at least one reinforcing material which is provided under at least the conductive layer and whose Young's modulus is 30 GPa or more; and
~~at least one~~ a plurality of first reinforcing ~~[[plug]]~~ plugs which ~~[[is]]~~ are connected to the conductive layer and which ~~[[is]]~~ are formed in contact with the reinforcing material;
wherein the plurality of first reinforcing plugs are arranged within 5 μ m from the conductive plug, and an interval between plugs including the respective first reinforcing plugs and the conductive plug is set to about 1 μ m or less.

2. - 4. (Canceled)

5. (Original) The device according to claim 1, wherein:
the insulating films and the reinforcing materials are stacked and arranged in two or more layers, respectively, and the conductive layers, the conductive plugs, and the first reinforcing plugs are provided with respect to the insulating films and the reinforcing materials of the respective layers.

CLAIM 6 (CANCELLED)

7. (Original) The device according to claim 1, further comprising:
a barrier metal film with which the conductive plug is coated and which contains a high-melting metal.

8. (Original) The device according to claim 1, wherein a Young's modulus of the insulating film of at least one layer is 20 GPa or less.

CLAIMS 9-23 (CANCELLED)